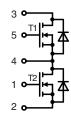


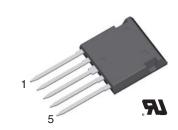
## HiPerFET™ Power MOSFET

Phaseleg Topology in ISOPLUS i4-PAC™

= 75 A= 100 V $R_{DSontyp.} = 18 m\Omega$ 

Preliminary data





MOSFET T1/T2				
Symbol	Conditions	Maximum Ratings		
V <sub>DSS</sub>	$T_{VJ} = 25^{\circ}C$ to $150^{\circ}C$	100	V	
$V_{GS}$		±20	V	
I <sub>D25</sub>	$T_{C} = 25^{\circ}C$ $T_{C} = 90^{\circ}C$	75 50	A A	
I <sub>F25</sub>	(body diode) $T_C = 25^{\circ}C$ (body diode) $T_C = 90^{\circ}C$	100 60	A A	
dv/dt	$V_{DS} < V_{DSS}; I_F \le 300A; \mid di_F/dt \mid \le 100A/\mu s; R_G = 2 \Omega T_{VJ} = 150^{\circ} C$	2 5	V/ns	
E <sub>AR</sub>	T <sub>C</sub> = 25°C	30	mJ	

Symbol		characteristic Values s otherwise specified)		
	$(1_{VJ} = 25 \text{ C}, \text{ unless})$		max.	
R <sub>DSon</sub>	$V_{GS} = 10 \text{ V}; I_D = I_{D90}$	18	25 mΩ	
$V_{\rm GSth}$	$V_{DS} = 20 \text{ V}; I_D = 4 \text{ mA}$ 2		4 V	
I <sub>DSS</sub>	$V_{DS} = V_{DSS}$ ; $V_{GS} = 0 \text{ V}$ ; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	0.25	0.3 mA mA	
GSS	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$		200 nA	
$egin{array}{c} \mathbf{Q}_{\mathrm{g}} \ \mathbf{Q}_{\mathrm{gs}} \ \mathbf{Q}_{\mathrm{gd}} \end{array}$	$ V_{GS} = 10 \text{ V; } V_{DS} = 0.5 \bullet V_{DSS}; I_{D} = I_{D90} $	180 35 85	nC nC nC	
$\begin{matrix} \mathbf{t}_{d(on)} \\ \mathbf{t}_{r} \\ \mathbf{t}_{d(off)} \\ \mathbf{t}_{f} \end{matrix}$	$\begin{cases} V_{GS} = 10 \text{ V; } V_{DS} = 0.5 \bullet V_{DSS} \\ I_{D} = I_{D90}; R_{G} = 2 \Omega \end{cases}$	20 60 80 60	ns ns ns ns	
$V_{F}$	(body diode) $I_F = 75 \text{ A}; V_{GS} = 0 \text{ V}$	1.2	1.5 V	
t <sub>rr</sub>	(body diode) $I_F = 37.5A$ ; -di/dt = 100A/ $\mu$ s; $V_{DS} = 25V$	300	ns	
$oldsymbol{R}_{thJC} \ oldsymbol{R}_{thJH}$	with heat transfer paste	0.93	0.5 K/W K/W	

IXYS reserves the right to change limits, test conditions and dimensions.

## **Features**

- HiPerFET™ technology
- low  $\mathbf{R}_{\mathrm{DSon}}$  low gate charge for high frequency operation
- unclamped inductive switching (UIS) capability
- dv/dt ruggedness
- fast intrinsic reverse diode
- ISOPLUS i4-PAC<sup>™</sup> package
  - isolated back surface
  - low coupling capacity between pins and heatsink
  - enlarged creepage towards heatsink
  - application friendly pinout
  - low inductive current path
  - high reliability
  - industry standard outline
  - UL registered E 72873

## **Applications**

- drives and power supplies
- battery or fuel cell powered
- automotive, industrial vehicle etc.
- secondary side of mains power supplies



Component					
Symbol	Conditions	Maximum R	Maximum Ratings		
T <sub>VJ</sub> T <sub>stg</sub>		-55+150 -55+125	°C °C		
V <sub>ISOL</sub>	I <sub>ISOL</sub> ≤ 1 mA; 50/60 Hz	2500	٧~		
F <sub>c</sub>	mounting force with clip	20120	N		

Symbol	Conditions	Ch min.	haracteristic Values .  typ.  max.		
C <sub>p</sub>	coupling capacity between shorted pins and mounting tab in the case		40	pF	
d <sub>s</sub> ,d <sub>A</sub> d <sub>s</sub> ,d <sub>A</sub>	pin - pin pin - backside metal	1.7 5.5		mm mm	
Weight			9	g	

